



## T0820H-6E 8A TRIAC

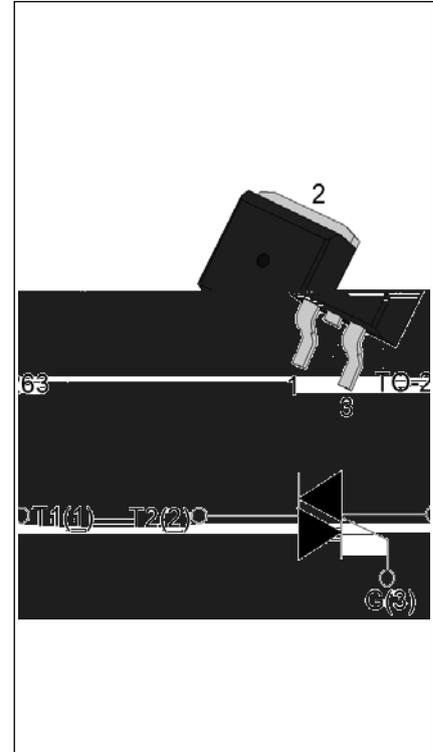
Rev.A.1.0

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The T0820H-6E triac is suitable for general purpose AC switching. It can be used as an ON/OFF function in applications such as heating regulation, induction motor starting circuits, for phase control operation in light dimmers, motor speed controllers. Compared to traditional triacs, T0820H-6E provides a very high switching capability up to junction temperatures of 150°C. Package TO-263 is RoHS compliant.

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Symbol	Value	Unit
$I_{T(RMS)}$	8	A
$V_{DRM}/V_{RRM}$	600	V
$I_{GT} / /$	20/20/20	mA



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Parameter	Symbol	Value	Unit
Storage junction temperature range	$T_{stg}$	-40-150	
Operating junction temperature range	$T_j$	-40-150	
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )	$V_{DRM}$	600	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )	$V_{RRM}$	600	V
RMS on-state current ( $T_c = 133^\circ\text{C}$ )	$I_{T(RMS)}$	8	A
Non repetitive surge peak on-state current (full cycle, $t_p=20\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I_{TSM}$	80	A
Non repetitive surge peak on-state current (full cycle, $t_p=16.6\text{ms}$ , $T_j=25^\circ\text{C}$ )		88	
$I^2t$ value for fusing ( $t_p=10\text{ms}$ , $T_j=25^\circ\text{C}$ )	$I^2t$	32	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 I_{GT}$ , $f=100\text{Hz}$ , $T_j=150^\circ\text{C}$ )	$di/dt$	80	$\text{A}/\mu\text{s}$
Peak gate current ( $t_p=20\mu\text{s}$ , $T_j=150^\circ\text{C}$ )	$I_{GM}$	4	A
Average gate power dissipation ( $T_j=150^\circ\text{C}$ )	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	10	W

Peak pulse voltage ( $T_j=25$ ; non-repetitive, off-state; FIG.8)	$V_{pp}$	3	kV
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( $T_j=25$  unless otherwise specified)

Symbol	Test Condition	Quadrant	Value		Unit
$I_{GT}$	$V_D=12V R_L=33$	- -	MAX.	20	mA
$V_{GT}$		- -	MAX.	1	V
$V_{GD}$	$V_D=V_{DRM} T_j=150$ $R_L=3.3K$	- -	MIN.	0.2	V
$I_L$	$I_G=1.2I_{GT}$	-	MAX.	40	mA
				55	
$I_H$	$I_T=100mA$		MAX.	30	mA
dV/dt	$V_D=400V$ Gate Open $T_j=150$		MIN.	1000	V/ $\mu s$
(dI/dt) <sub>c</sub>	(dV/dt) <sub>c</sub> =20V/ $\mu s$ , $T_j=150$		MIN.	3	A/ms
$t_{on}$	$I_G=40mA I_A=200mA I_R=20mA$ $T_j=25$		TYP.	3	$\mu s$
$t_{off}$				30	

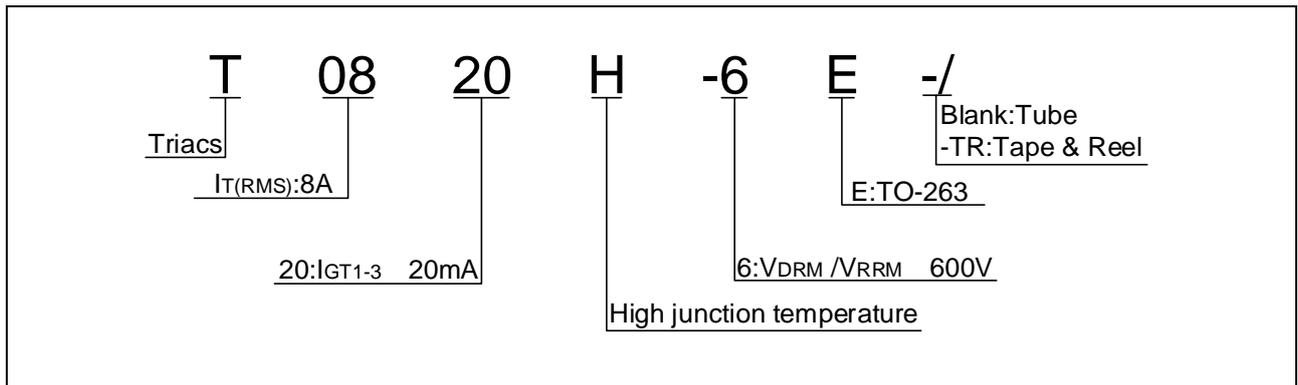
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Symbol	Parameter		Value(MAX.)	Unit
$V_{TM}$	$I_{TM}=11A t_p=380\mu s$	$T_j=25$	1.4	V
$V_{TO}$	Threshold voltage	$T_j=150$	0.79	V
$R_D$	Dynamic resistance	$T_j=150$	51	
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25$	5	$\mu A$
$I_{RRM}$		$T_j=150$	1	mA

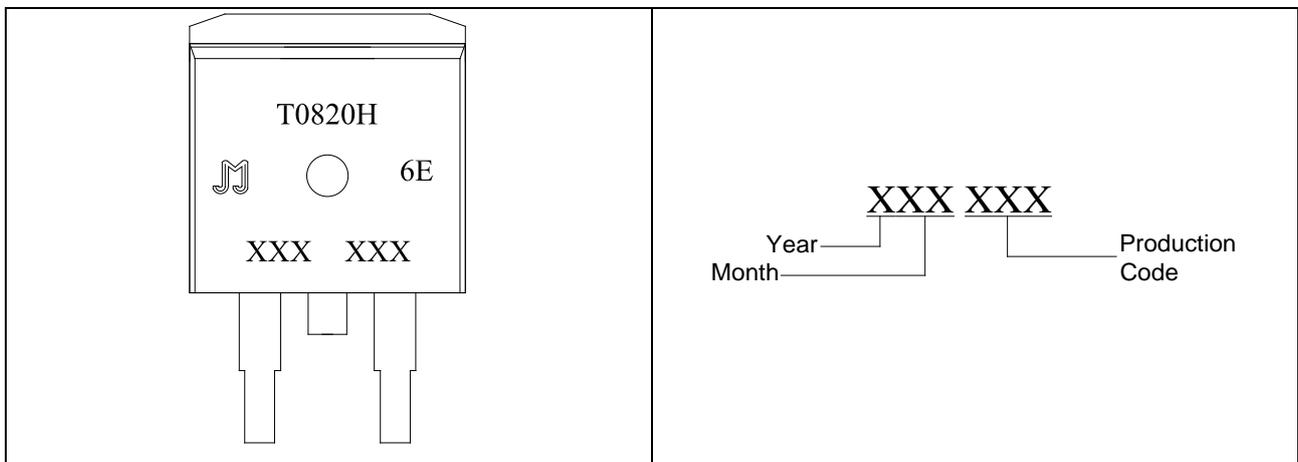
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Symbol	Parameter	Value	Unit
$R_{th(j-c)}$	junction to case (AC)	1.6	$\text{W}$
$R_{th(j-a)}$	junction to ambient (AC, in free air, $S=2cm^2$ )	45	$\text{W}$

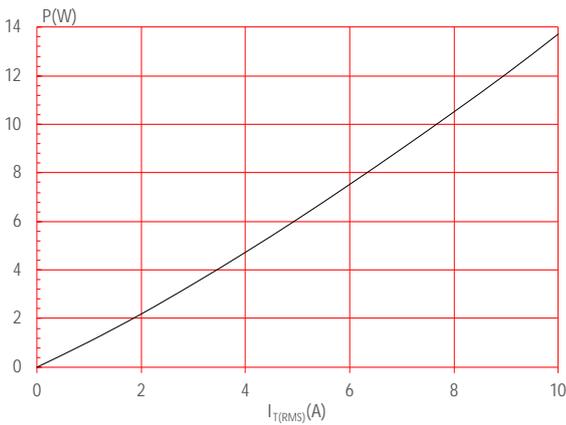
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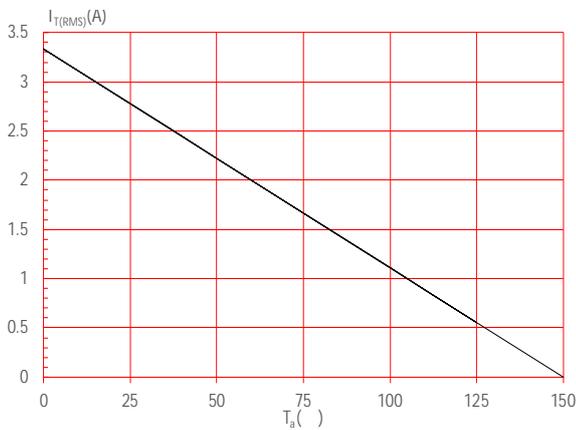
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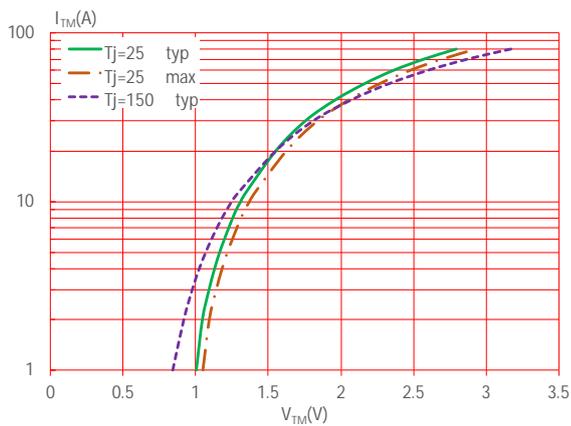
**FIG.1** Maximum power dissipation versus RMS on-state current



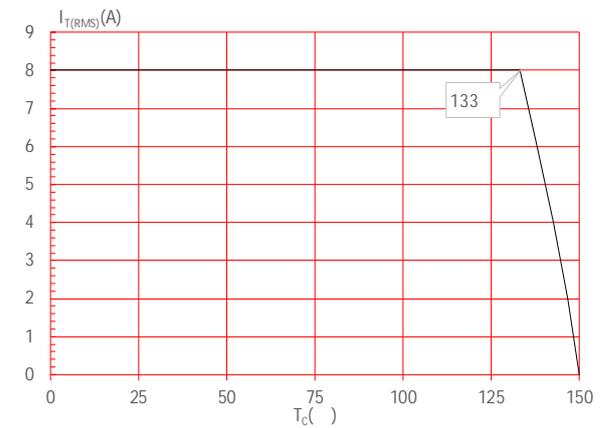
**FIG.3:** RMS on-state current versus ambient temperature (printed circuit board FR4,copper thickness:35μm)(full cycle)



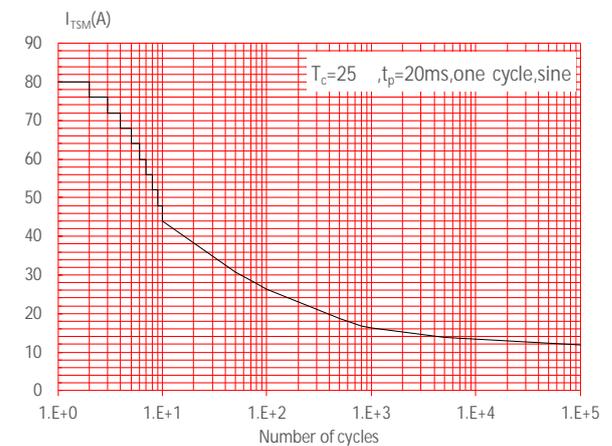
**FIG.5:** On-state characteristics



**FIG.2:** RMS on-state current versus case temperature



**FIG.4:** Surge peak on-state current versus number of cycles



**FIG.6:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $I^2t$  ( $di/dt < 80\text{A}/\mu\text{s}$ )

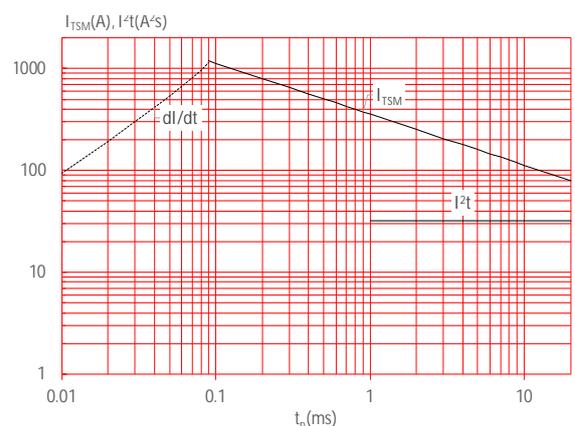
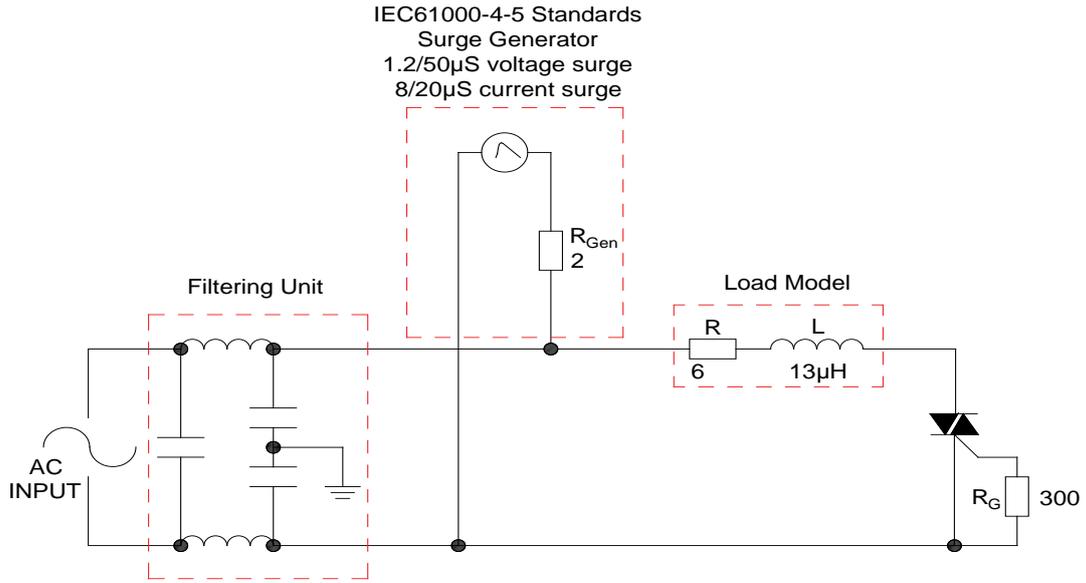


FIG.7:

FIG.8 Test circuit for inductive and resistive loads to IEC-61000-4-5 standards



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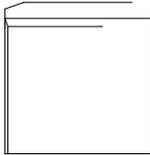
Reflow Condition	Pb-Free assembly (see figure at right)
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-Temperature Min ( $T_{s(min)}$ )    +150

Pre  
Heat



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Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	9.90		10.20	0.390		0.402
B	14.70		15.80	0.579		0.622
C	9.40		9.60	0.37		0.378
D	2.40			0.094		
E	1.20		1.50	0.047		0.059
F	0.75		0.85	0.029		0.033
G			1.50			
H	4.40		4.70	0.173		0.185
J	2.30		2.70	0.091		0.106
K	0.38		0.55	0.015		0.022
L	0		0.25			
M	1.25		1.35			



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